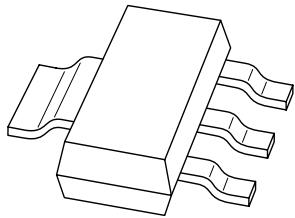


# DATA SHEET



## **PZTA92** PNP high-voltage transistor

Product specification  
Supersedes data of 1997 May 22

1999 Apr 14



## PNP high-voltage transistor

## PZTA92

## FEATURES

- Low current (max. 100 mA)
- High voltage (max. 300 V).

## APPLICATIONS

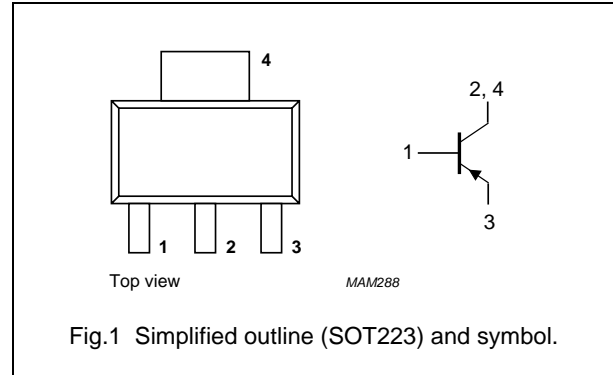
- Video equipment
- Telephony
- Professional communication equipment.

## DESCRIPTION

PNP high-voltage transistor in a SOT223 plastic package.  
NPN complement: PZTA42.

## PINNING

PIN	DESCRIPTION
1	base
2, 4	collector
3	emitter



## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	–300	V
$V_{CEO}$	collector-emitter voltage	open base	–	–300	V
$V_{EBO}$	emitter-base voltage	open collector	–	–5	V
$I_C$	collector current (DC)		–	–100	mA
$I_{CM}$	peak collector current		–	–200	mA
$I_{BM}$	peak base current		–	–100	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$ ; note 1	–	1.2	W
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C
$T_{amb}$	operating ambient temperature		–65	+150	°C

## Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>. For other mounting conditions, see “*Thermal considerations for SOT223 in the General Part of associated Handbook*”.

## PNP high-voltage transistor

PZTA92

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	104	K/W
$R_{th\ j-s}$	thermal resistance from junction to soldering point		23	K/W

## Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>. For other mounting conditions, see "Thermal considerations for SOT223 in the General Part of associated Handbook".

## CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$I_{CBO}$	collector cut-off current	$I_E = 0; V_{CB} = -200\text{ V}$	–	–20	nA
$I_{EBO}$	emitter cut-off current	$I_C = 0; V_{BE} = -5\text{ V}$	–	–100	nA
$h_{FE}$	DC current gain	$I_C = -1\text{ mA}; V_{CE} = -10\text{ V}; \text{note 1}$	25	–	
		$I_C = -10\text{ mA}; V_{CE} = -10\text{ V}; \text{note 1}$	40	–	
		$I_C = -30\text{ mA}; V_{CE} = -10\text{ V}; \text{note 1}$	25	–	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -20\text{ mA}; I_B = -2\text{ mA}$	–	–500	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = -20\text{ mA}; I_B = -2\text{ mA}$	–	–900	mV
$C_C$	collector capacitance	$I_E = 0; V_{CB} = -20\text{ V}; f = 1\text{ MHz}$	–	6	pF
$f_T$	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -20\text{ V}; f = 100\text{ MHz}$	50	–	MHz

## Note

1. Pulse test:  $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$ .

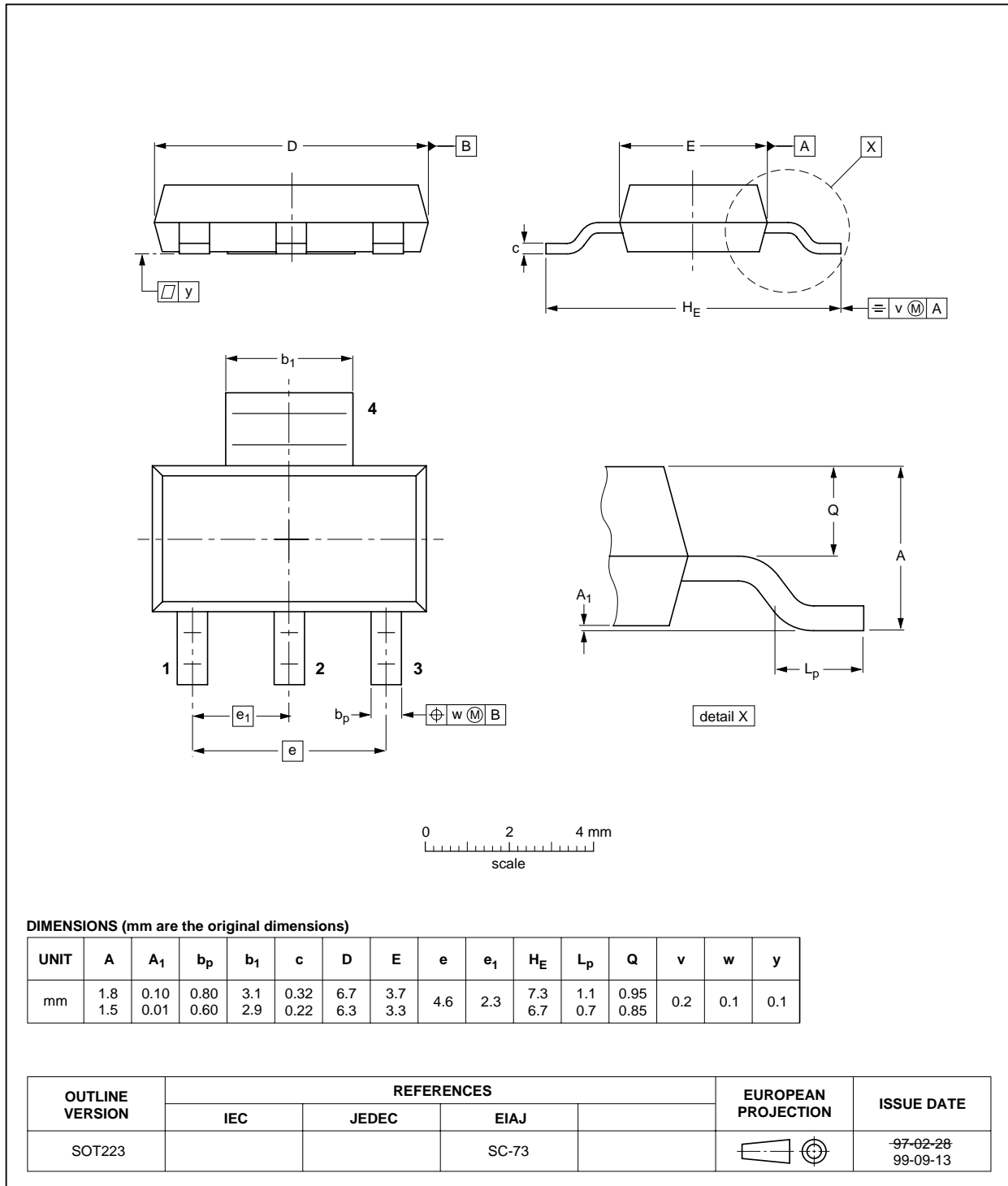
PNP high-voltage transistor

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PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223



## PNP high-voltage transistor

PZTA92

## DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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## **Contact information**

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